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# Physicochemical and optical characterization of As-Se-Ag glassy materials

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Seventh National Conference on Chemistry, 26–29 May 2011, Sofia, Bulgaria

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# Multicomponent chalcogenide glasses







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Glasses based on As and Se — interesting electrical and optical properties Selenium-based chalcogenide glasses - promising materials for optical applications — high refractive index

Fabrication of optical fibers for infrared region

good transparency in the infrared region







# **Objective of investigation:**

- Study of compositional dependence of basic physicochemical parameters in As-Se-Ag chalcogenide glasses.
- Study of optical characteristics of thin (AsSe)<sub>100-x</sub>Ag<sub>x</sub> films, deposited by two different methods, VTE and PLD, from the corresponding bulk materials. Evaluation of their dependence on composition, namely on silver amount added to the amorphous glassy matrix.





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Scheme of the experiment Glass preparation Structural study

**Study of physicochemical behaviors** 

Density Microhardness Molar volume Compactness

**Deposition of thin films** 

**Optical characterization** 





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## **Compositions**

# AsSe

### with 0, 5, 10, 15, 20, 25 mol.% Ag

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### **Preparation of glasses: Melt quenching technique**

Heating the material to (or above) the melting point (Tm)

cooling the molten form sufficiently quickly.

- > Cooling media: mixture of cool water, ice and NaCl.
- > Selection of cooling mode depends on structure, type, and volume of the material.
- > The main feature of the melt-quenching process is that the amorphous solids are formed by continuous hardening (i.e. increase in viscosity) of the melt.

### **Synthesis of As-Se-Ag glasses:**

- First step: Preparation of binary AsSe glass in quartz ampoules evacuated down to ~10<sup>-3</sup> Pa and heated in a rotary furnace up to melting temperature of As. After a few hours the melt was quenched in a mixture of ice and water.
- Second step: Preparation of silver containing glasses from AsSe and silver at heating up to 900°C and quenching in a mixture of ice and water.





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# XRD





**SEM** 

Smooth and homogeneous structure of the samples. Samples with 25 mol% Ag do not show any silver clusters concentrated into the glassy matrix.





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# **IR** spectra



basic bands  $220 \text{ cm}^{-1} \longrightarrow \text{AsSe}_3$   $232 \text{ cm}^{-1} \longrightarrow \text{Ag}_3\text{AsSe}_3$   $256 \text{ cm}^{-1} \longrightarrow \text{Se} - \text{Se}$  chains  $350 \text{ cm}^{-1} \longrightarrow \text{Se}_8$  rings

Structural units with very closed vibrational modes.

The main reason for the strong overlap of the vibrational modes is proximity in the masses of As and Se atoms and similar bond strengths of the As-Se and Se-Se bonds.





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 $x_i$  – atomic fraction of the i-th component of a glass;;  $\rho$  – experimental density;  $x_i$  – atomic fraction of the components;  $A_i$  – atomic weight of the components;

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Compactness (δ)
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$$\delta = \left(\sum_{i} \frac{\mathbf{x}_{i} \mathbf{A}_{i}}{\boldsymbol{\rho}_{i}} - \sum_{i} \frac{\mathbf{x}_{i} \mathbf{A}_{i}}{\boldsymbol{\rho}}\right) \cdot \left(\sum_{i} \frac{\mathbf{x}_{i} \mathbf{A}_{i}}{\boldsymbol{\rho}}\right)^{-1}$$

### Microhardness (Hµ)

 $H\mu = P/Ad^2$ 

P is applied load, kgf; d [mm] – the length of the longer diagonal imprint; A-technological parameter equal to 0.07028





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absence of any deflections in  $\rho$  and  $H\mu -si$  is well incorporated in the chalcogenide matrix and uniformly distributed.

Introduction of silver atoms leads to formation of Ag-containing structural configurations (IR spectra), changing the glass structure. As a result, the network stability of the glasses is improved, and the structure gets more dense and compact.



### **Physicochemical parameters - theoretically calculated**



 $\rightarrow$  Average coordination number  $\langle Z \rangle$  - average number of bonds/atom, which must be broken to obtain fluidity. <Z>=f (nearest neighbour atoms for As, Se and Ag); ZAg= 3; ZAs = 3; ZSe = 2;  $\langle \mathbf{Z} \rangle = \sum_{i} x_i Z_i$ 

 $x_i$  – atomic fraction of the i-th component of a glass;  $Z_1$  – coordination number of the i-th atom;

7 ~	24	
_>	2.4	
		N

**Phillips and Thorpe theory:** When Z > 2.40, the solid has continuously connected rigid regions with floppy regions inter-dispersed and may be termed as 'amorphous' solid.

### > Number of constrains per atom (Nco)

Nco = Na + Nb = Z/2 + (2Z - 3) - Thorpe equation

Na and Nb are the radial and the axial bond strengths;

For the ideal glass, Nco=Nd=3, where the mechanical stability of the network is optimized.

As-Se-Ag glasses  $\longrightarrow$  Nco  $\approx 3$ 

Composition	Z	N <sub>CO</sub>	<e>,</e>
			eV
As <sub>50</sub> Se <sub>50</sub>	2.5	3.25	2.65
As <sub>47,5</sub> Se <sub>47,5</sub> Ag <sub>5</sub>	2.525	3.3	2.73
$As_{45}Se_{45}Ag_{10}$	2.55	3.38	2.81
As <sub>42,5</sub> Se <sub>42,5</sub> Ag <sub>15</sub>	2.575	3.44	2.89
$As_{40}Se_{40}Ag_{20}$	2.6	3.5	2.97
As <sub>37,5</sub> Se <sub>37,5</sub> Ag <sub>25</sub>	2.625	3.56	3.04

> Overall mean bond energy Ec - mean bond energy of the average cross-linking/atom (heteropolar bond energy);  $\langle E \rangle = Ec + Erm - Tichy equation$ Erm - average bond energy per atom of the 'remaining matrix' (homopolar bond energy)  $\langle E \rangle = f(\langle Z \rangle, the type and energy of bonds-heteropolar and homopolar)$ 

<E>↑ with Ag addition, due to formation of stronger heteropolar bonds. As a result, the network stability of the system increases, confirming the tendency of compositional dependence of experimentally derived physico-chemical parameters.





# Amorphous chalcogenide films

**Unique properties** 

transparent in the infrared region of the spectrum

**Opportunity for application** 

photo-induced structural changes under action of light with photon energy greater than band gaps of the materials.

optical waveguides with different geometry, applicable in mid-IR fiber-optic sensing.

changes in the optical constants  $(\Delta n, \Delta k)$ and physicochemical properties (microhardness, density, solubility).

<u>Planar waveguide</u>

 $N_{core \ layer} \neq N_{cladding \ layer}$  - obtained by direct writing with light on the surface of the material.





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### **Preparation of thin amorphous chalcogenide films:**

- > Vacuum thermal evaporation
- Pulsed laser deposition

### **Results:**

- > Transmission spectra recorded within the spectral range (400–2500 nm)
- **Refractive index (n) Swanepoel method.**
- > Determination of Eg from absorption coefficient data by Tauc procedure.
- Influence of the Ag content on the optical band gap of the films prepared by PLD and VTE.
- Spectral dispersion of the refractive index of the films with different Ag contents, prepared by PLD and VTE.





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### **Preparation of thin As-Se-Ag films: Vacuum thermal evaporation**



### **CONDITIONS OF VTE PROCESS**

- > source-substrate distance 0.12 m
- > temperature of evaporation source 700–800 K
- > temperature of the substrates 300 K
- ➤ residual gas pressure of 10<sup>-5</sup> Torr

### Thin films for optical measurements:

deposited on glass substrates d ~ 800–900 nm





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### **Advantages of PLD:**

- relative simplicity of the process
- nearly stoichiometric transfer of target material to the films
- easy control of the process by laser operating parameters and possibility to prepare films of unusual compositions



### **CONDITIONS OF THE PLD PROCESS**

 $P = 10^{-4} Pa$ KrF\* excimer laser,  $\lambda = 248$  nm;  $\tau = 25$  ns; F = 1.6 J/cm2, N = 3000 deposition rate = 1.5–3.0 Å/pulse





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The red shift of the abs. edge after addition of silver is caused by formation of additional defect states, localized just above the valence band.

### Transmission spectra recorded within the spectral range 400–2500 nm

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Absorption coefficient  $\alpha$ :  $\alpha = 1/d [\ln (1-R)^2 / T]$ 

d – thickness of the film

R – reflectivity of the film

### Absorption coefficient of amorphous semiconductors:

 $(\alpha hv) = B\{hv - Eg\}^m$ 

**Determination of the Eg values** Tauc procedure: plotting a graph of  $(\alpha hv)^{1/2}$  versus hv  $\rightarrow$  extrapolation of the straight line part to the energy axis of zero absorption coefficient





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### Influence of the Ag content on the optical band gap of amorphous (AsSe)<sub>100-x</sub>Ag<sub>x</sub> films prepared by PLD and VTE.



Eg  $\downarrow$  with increase of Ag - structural transformation and bond rearrangement in the films. The atomic substitution of As by Ag probably causes an increase in disorder and the amount of defects present in amorphous structure, resulting in optical band gap decrease.

Eg(VTE) > Eg(PLD) due to the preparation technique, providing difference in the structure of the obtained films: Due to higher temperature and energy of the particles in the plume, the structure of PLD films can be closer to statistically disordered model of amorphous solids (**P. Ne<sup>\*</sup>mec et al.** / **Thin Solid Films 484 (2005) 140–145).** This distortion in the structure leads to higher Eg values of VTE thin films.





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- The increase of n is related to higher polarizability of larger Ag atoms, compared to Se atoms.
- The refractive index n of PLD films is slightly higher as compared to VTE films, due to the different structure.





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### Conclusions

- > The obtained materials exhibit homogeneous and glassy structure in a wide range of composition.
- Density results show that the silver atoms are well incorporated in the chalcogenide matrix and uniformly distributed.
- > Stability in the behaviors and silver dispersion provide good network stability of the obtained materials.
- Thin amorphous (AsSe)<sub>100-x</sub>Ag<sub>x</sub> films were obtained by VTE and PLD techniques, and their optical properties were investigated.
- > A red shift of the absorption edge is observed upon addition of Ag to the glassy matrix.
- The observed decrease in the optical band gap with the increase of Ag concentration was attributed to structural transformation and bond rearrangement in the films. The atomic substitution of As for Ag probably caused an increase in disorder and the amount of defects present in amorphous structure, thus decreasing the optical band gap.
- Refractive index calculations showed that PLD films have a slightly higher index of refraction as compared to the VTE films. The increase of the refractive index with Ag content in both types of films is probably related to the higher polarizability of the larger Ag atoms.

# Thank you!





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# Why Ag-As-Se glasses?

- ➤ Ag → additives in network glasses, such as chalcogenides and oxides, because the resulting glasses can show high electrical conductivities with potential applications for batteries, sensors and displays.



Ζ

 $Z_{i} = 8 - N$ 

### **Physicochemical parameters: theoretically calculated**



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 $x_i$  – atomic fraction of the i-th component of a glass;  $Z_1$  – coordination number of the i-th atom;  $N_i$  – number of electrons in the outer shell of the atom;

$$= Z_{Ag}x + Z_{As}y + Z_{Se}z \qquad Z > 2.4$$
Phillips and Thorpe theory:

> Glasses with Z < 2.40 consist of rigid regions, immersed in a 'floppy' matrix.

> Glasses with Z = 2.40 are unique - the floppy and the rigid regions are individually connected with a maximum number of connections.

 $\rightarrow$  When Z > 2.40, the solid has continuously connected rigid regions with floppy regions inter-dispersed and may be termed as 'amorphous' solid.

> Number of constrains per atom (Nco)

Nco = Na + Nb = Z/2 + (2Z - 3) - Thorpe equation

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**Thickness of As-Se-Ag films** 



The thickness decrease with Ag percentage could be attributed to an increase of the reflectivity on addition of Ag, which makes the laser beam energy transfer to the target more difficult.